

AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A method for removing particles on semiconductor wafers comprising:

dipping semiconductor wafers in a cleaning solution tank to which a cleaning solution is fed;

feeding ultrasonic waves into the cleaning solution after the passage of a prescribed period of time since the time that the semiconductor wafers are dipped in the cleaning solution;

wherein the prescribed period of time is more than 5 sec.

2. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 1 wherein the prescribed time is 20 sec or more.

3. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 1 wherein the prescribed time corresponds to a substitution ratio of the cleaning solution in the cleaning solution tank of 0.4 or more.

4. (Currently Amended) The method for removing particles on semiconductor wafers described in Claim 2 wherein ~~the feeding time of the a~~ time for the feeding ultrasonic waves into the cleaning solution is 400 sec or more.

5. (Currently Amended) The method for removing particles on semiconductor wafers described in Claim 4 wherein the a total cleaning time for the semiconductor wafers is 600 sec or more.

6. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 1 wherein the cleaning solution is ultra-pure water.

7. (Previously Presented) The method for removing particles on semiconductor wafer described in Claim 1 wherein the cleaning solution is hydrogen-enriched ultra-pure water.

8. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 7 wherein a concentration of hydrogen in the hydrogen-enriched ultra-pure water is in the range of 0.3-1.6 ppm.

9. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 1 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

10. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 2 wherein the cleaning solution is ultra-pure water.

11. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 2 wherein the cleaning solution is hydrogen-enriched ultra-pure water.

12. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 3 wherein the cleaning solution is hydrogen-enriched ultra-pure water.

13. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 4 wherein the cleaning solution is hydrogen-enriched ultra-pure water.

14. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 5 wherein the cleaning solution is hydrogen-enriched ultra-pure water.

15. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 2 wherein the step of cleaning semiconductor wafer ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

16. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 3 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

17. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 4 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

18. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 5 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

19. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 6 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.

20. (Previously Presented) The method for removing particles on semiconductor wafers described in Claim 7 wherein the step of cleaning semiconductor wafers ultrasonically is performed after the step of cleaning semiconductor wafers by means of a cleaning solution mainly comprising hydrogen fluoride.